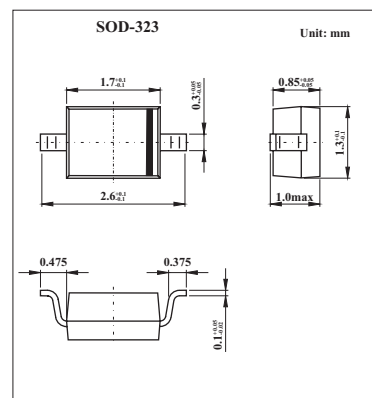


Silicon Epitaxial Planar Diode

MA2ZV03

■ Features

- Good linearity and large capacitance-ratio in C_D - V_R relation
- Small series resistance r_D
- S-mini type package, allowing downsizing of equipment and automatic insertion through the taping package

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse voltage (DC)	V_R	6	V
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 5\text{ V}$			10	nA
Diode capacitance	$C_{D(1V)}$	$f = 1\text{ MHz}; V_R = 1\text{ V}$	5.2		5.8	pF
	$C_{D(4V)}$	$f = 1\text{ MHz}; V_R = 4\text{ V}$	2.1		2.58	
Capacitance ratio	$C_{D(1V)}/C_{D(4V)}$		2.1		2.6	
Series resistance *	r_s	$V_R = 4\text{ pF}, f = 470\text{ MHz}$		1.9	0.3	Ω

Note :

1. Rated input/output frequency: 470 MHz
2. * : rf measuring instrument: YHP MODEL 4191A RF IMPEDANCE ANALYZER

■ Marking

Marking	7Z
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